TOSHIBA Field Effect Transistor Silicon P Channel Junction Type

2SJ103

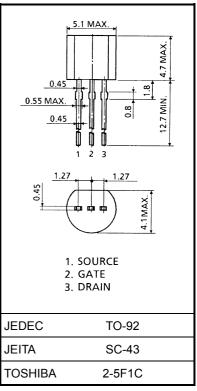
For Audio Amplifier, Analog Switch, Constant Current and Impedance Converter Applications

- High breakdown voltage: $V_{GDS} = 50 \text{ V}$
- High input impedance: $I_{GSS} = 1.0 \text{ nA (max) (V}_{GS} = 30 \text{ V)}$
- Low RDS (ON): RDS (ON) = 270 Ω (typ.) (IDSS = -5 mA)
- Complimentary to 2SK246

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	50	V
Gate current	IG	-10	mA
Drain power dissipation	P_{D}	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Unit: mm

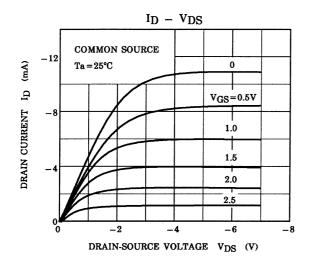


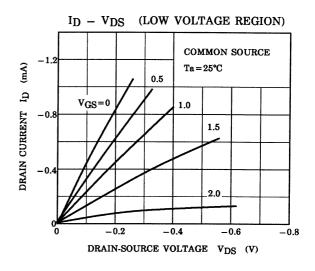
Weight: 0.21 g (typ.)

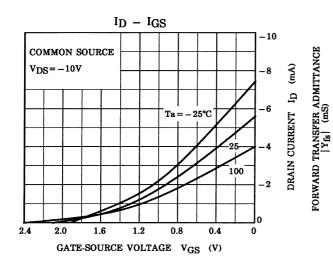
Electrical Characteristics (Ta = 25°C)

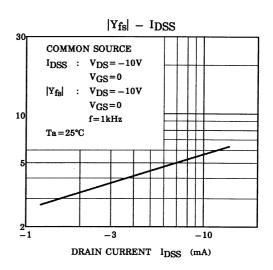
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = 30 \text{ V}, V_{DS} = 0$	_	_	1.0	nA
Gate-drain breakdown voltage	V _{(BR) GDS}	$V_{DS} = 0$, $I_G = 100 \mu A$	50	_	_	٧
Drain current	I _{DSS} (Note)	$V_{DS} = -10 \text{ V}, V_{GS} = 0$	-1.2	_	-14	mA
Gate-source cut-off voltage	V _{GS (OFF)}	$V_{DS} = -10 \text{ V}, I_D = -0.1 \mu\text{A}$	0.3	_	6.0	٧
Forward transfer admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	1.0	4.0	_	mS
Drain-source ON resistance	R _{DS (ON)}	$V_{DS} = -10 \text{ mV}, V_{GS} = 0, I_{DSS} = -5 \text{ mA}$		270		Ω
Input capacitance	C _{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		18	_	pF
Reverse transfer capacitance	C _{rss}	$V_{DG} = -10 \text{ V}, I_D = 0, f = 1 \text{ MHz}$		3.6	_	pF

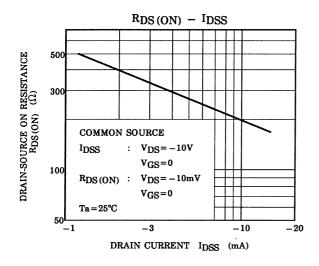
Note: IDSS classification Y: $-1.2\sim-3.0$ mA, GR: $-2.6\sim-6.5$ mA, BL: $-6\sim-14$ mA

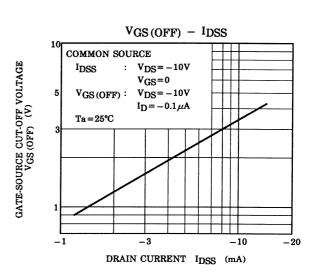


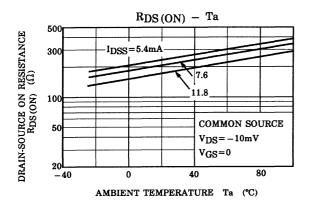


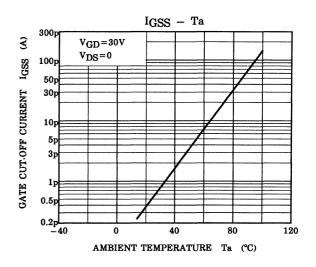


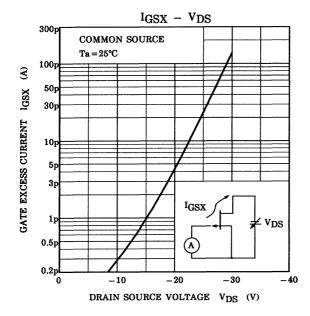


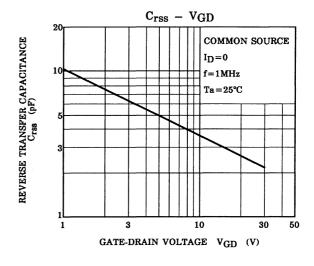


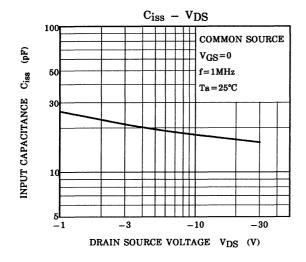


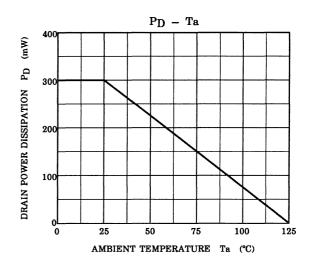












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